

PDP TRENCH IGBT

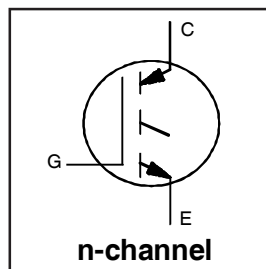
IRG7S313UPbF

Features

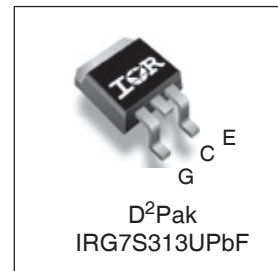
- Advanced Trench IGBT Technology
- Optimized for Sustain and Energy Recovery circuits in PDP applications
- Low $V_{CE(on)}$ and Energy per Pulse (E_{PULSE}^{TM}) for improved panel efficiency
- High repetitive peak current capability
- Lead Free package

Key Parameters

$V_{CE\ min}$	330	V
$V_{CE(on)}\ typ.\ @\ I_C = 20A$	1.35	V
$I_{RP}\ max\ @\ T_C = 25^\circ C$	160	A
$T_J\ max$	150	$^\circ C$



n-channel



D²Pak
IRG7S313UPbF

G	C	E
Gate	Collector	Emitter

Description

This IGBT is specifically designed for applications in Plasma Display Panels. This device utilizes advanced trench IGBT technology to achieve low $V_{CE(on)}$ and low E_{PULSE}^{TM} rating per silicon area which improve panel efficiency. Additional features are 150 $^\circ C$ operating junction temperature and high repetitive peak current capability. These features combine to make this IGBT a highly efficient, robust and reliable device for PDP applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GE}	Gate-to-Emitter Voltage	± 30	V
$I_C\ @\ T_C = 25^\circ C$	Continuous Collector Current, $V_{GE}\ @\ 15V$	40	A
$I_C\ @\ T_C = 100^\circ C$	Continuous Collector, $V_{GE}\ @\ 15V$	20	
$I_{RP}\ @\ T_C = 25^\circ C$	Repetitive Peak Current ①	160	
$P_D\ @\ T_C = 25^\circ C$	Power Dissipation	78	W
$P_D\ @\ T_C = 100^\circ C$	Power Dissipation	31	
	Linear Derating Factor	0.63	W/ $^\circ C$
T_J	Operating Junction and	-40 to + 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature for 10 seconds	300	

Thermal Resistance

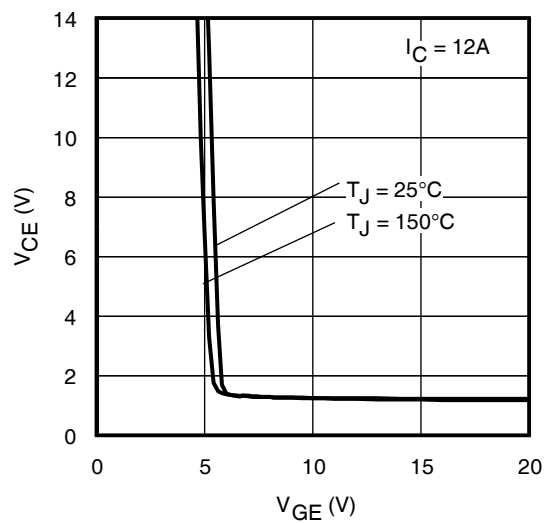
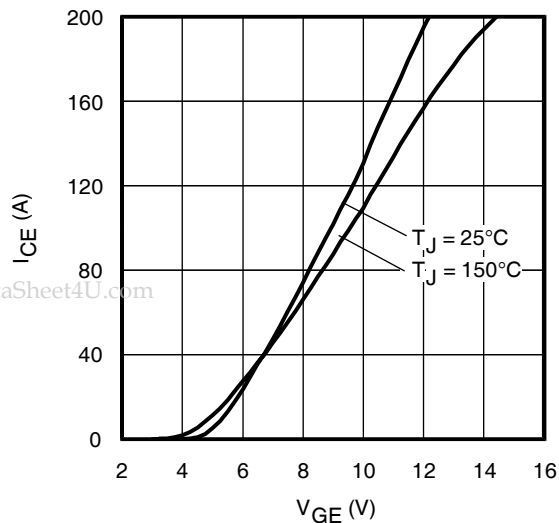
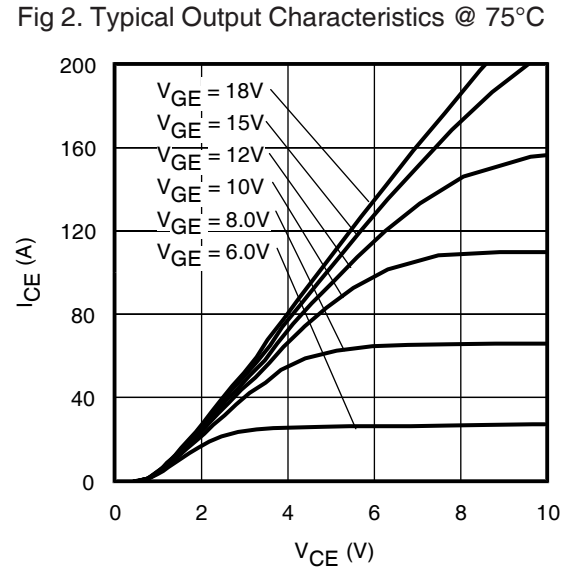
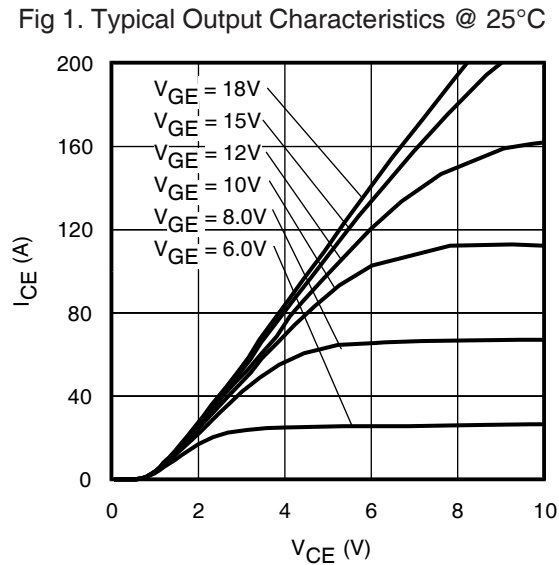
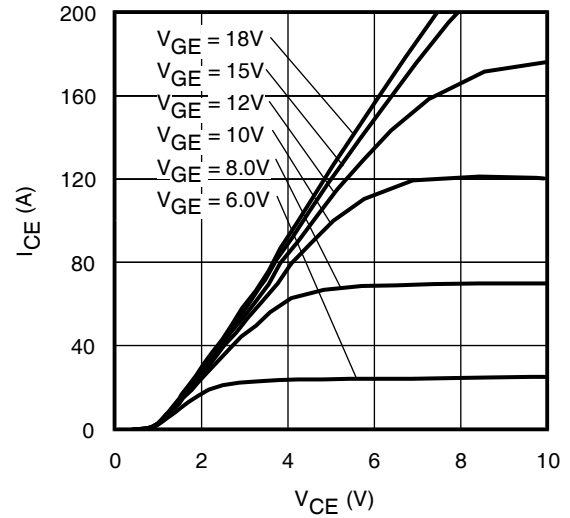
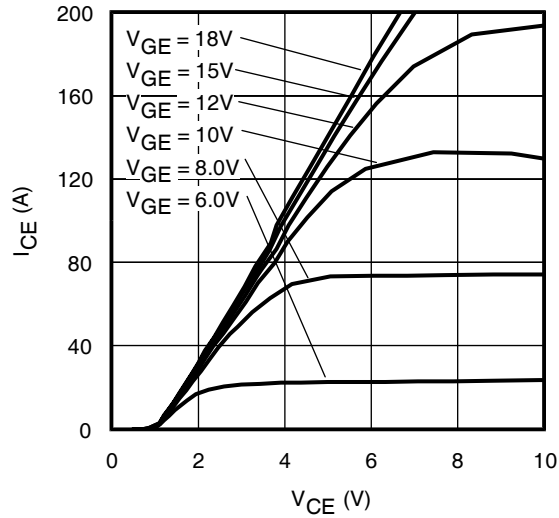
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ②	—	1.6	$^\circ C/W$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{CES}	Collector-to-Emitter Breakdown Voltage	330	—	—	V	V _{GE} = 0V, I _{CE} = 250μA
ΔBV _{CES} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.4	—	V/°C	Reference to 25°C, I _{CE} = 1mA
V _{CE(on)}	Static Collector-to-Emitter Voltage	—	1.21	1.45	V	V _{GE} = 15V, I _{CE} = 12A ③
		—	1.35	—		V _{GE} = 15V, I _{CE} = 20A ③
		—	1.75	—		V _{GE} = 15V, I _{CE} = 40A ③
		—	2.14	—		V _{GE} = 15V, I _{CE} = 60A ③
		—	1.41	—		V _{GE} = 15V, I _{CE} = 20A, T _J = 150°C ③
V _{GE(th)}	Gate Threshold Voltage	2.2	—	4.7	V	V _{CE} = V _{GE} , I _{CE} = 1.0mA
ΔV _{GE(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-10	—	mV/°C	
I _{CES}	Collector-to-Emitter Leakage Current	—	1.0	10	μA	V _{CE} = 330V, V _{GE} = 0V
		—	25	150		V _{CE} = 330V, V _{GE} = 0V, T _J = 125°C
		—	75	—		V _{CE} = 330V, V _{GE} = 0V, T _J = 150°C
I _{GES}	Gate-to-Emitter Forward Leakage	—	—	100	nA	V _{GE} = 30V
	Gate-to-Emitter Reverse Leakage	—	—	-100	nA	V _{GE} = -30V
g _{fe}	Forward Transconductance	—	47	—	S	V _{CE} = 25V, I _{CE} = 12A
Q _g	Total Gate Charge	—	33	—	nC	V _{CE} = 240V, I _C = 12A, V _{GE} = 15V③
Q _{gc}	Gate-to-Collector Charge	—	12	—		
t _{d(on)}	Turn-On delay time	—	1.0	—	ns	I _C = 12A, V _{CC} = 196V R _G = 10Ω, L=210μH T _J = 25°C
t _r	Rise time	—	13	—		
t _{d(off)}	Turn-Off delay time	—	65	—		
t _f	Fall time	—	68	—		
t _{d(on)}	Turn-On delay time	—	11	—	ns	I _C = 12A, V _{CC} = 196V R _G = 10Ω, L=200μH, L _S = 150nH T _J = 150°C
t _r	Rise time	—	14	—		
t _{d(off)}	Turn-Off delay time	—	86	—		
t _f	Fall time	—	190	—		
t _{st}	Shoot Through Blocking Time	100	—	—	ns	V _{CC} = 240V, V _{GE} = 15V, R _G = 5.1Ω
E _{PULSE}	Energy per Pulse	—	480	—	μJ	L = 220nH, C= 0.20μF, V _{GE} = 15V V _{CC} = 240V, R _G = 5.1Ω, T _J = 25°C
		—	570	—		L = 220nH, C= 0.20μF, V _{GE} = 15V V _{CC} = 240V, R _G = 5.1Ω, T _J = 100°C
ESD	Human Body Model	Class 1C (Per JEDEC standard JESD22-A114)				
	Machine Model	Class B (Per EIA/JEDEC standard EIA/JESD22-A115)				
C _{ies}	Input Capacitance	—	880	—	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	—	47	—		V _{CE} = 30V
C _{res}	Reverse Transfer Capacitance	—	26	—		f = 1.0MHz
L _C	Internal Collector Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.)
L _E	Internal Emitter Inductance	—	7.5	—		from package and center of die contact

Notes:

- ① Half sine wave with duty cycle = 0.05, $t_{on} = 2\mu\text{sec}$.
- ② R_θ is measured at T_J of approximately 90°C .
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.



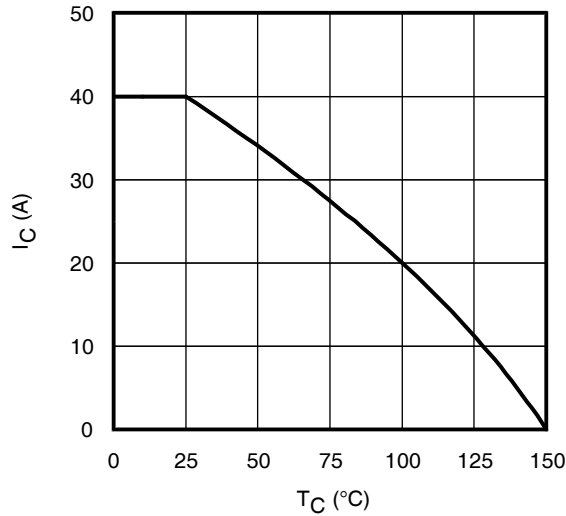


Fig 7. Maximum Collector Current vs. Case Temperature

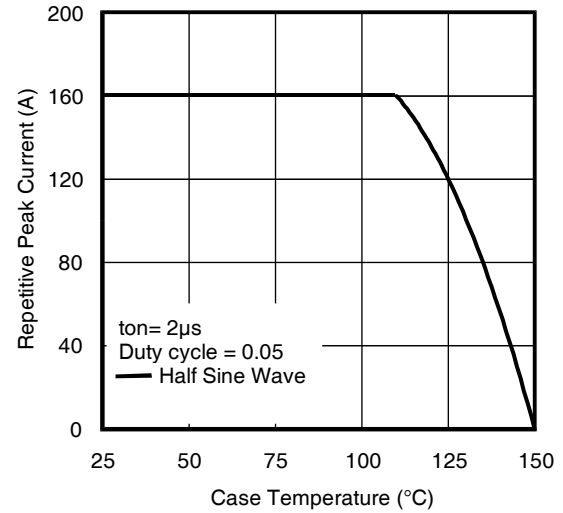


Fig 8. Typical Repetitive Peak Current vs. Case Temperature

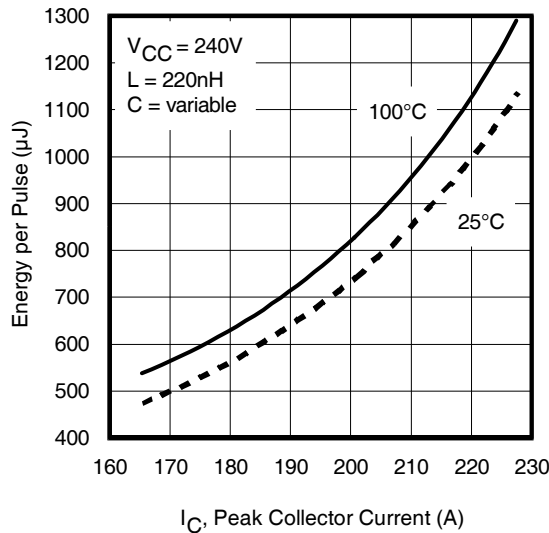


Fig 9. Typical E_{PULSE} vs. Collector Current

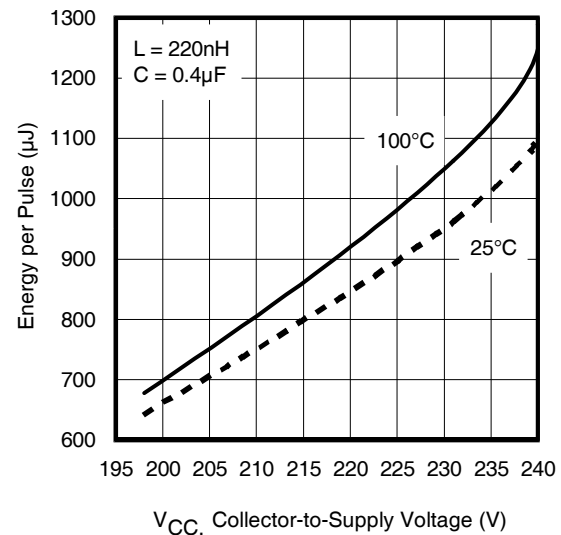


Fig 10. Typical E_{PULSE} vs. Collector-to-Supply Voltage

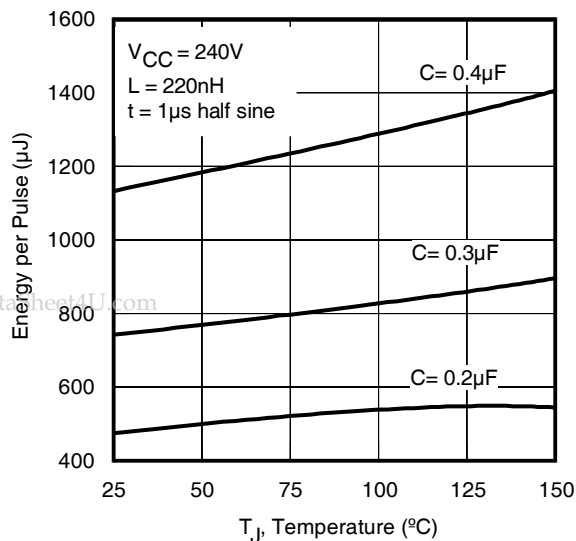


Fig 11. E_{PULSE} vs. Temperature

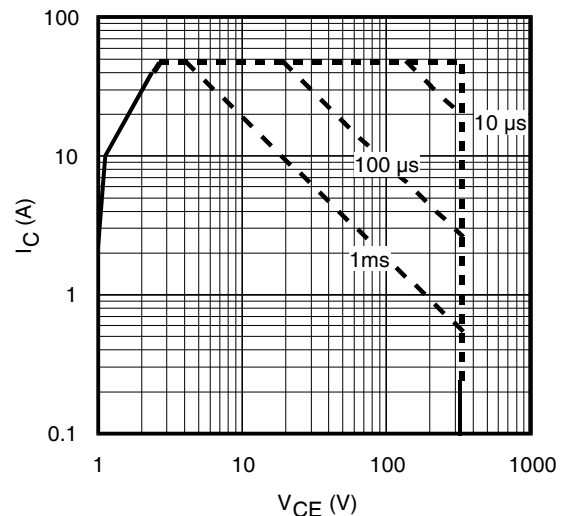


Fig 12. Forward Bias Safe Operating Area
www.DataSheet4U.com
www.irf.com

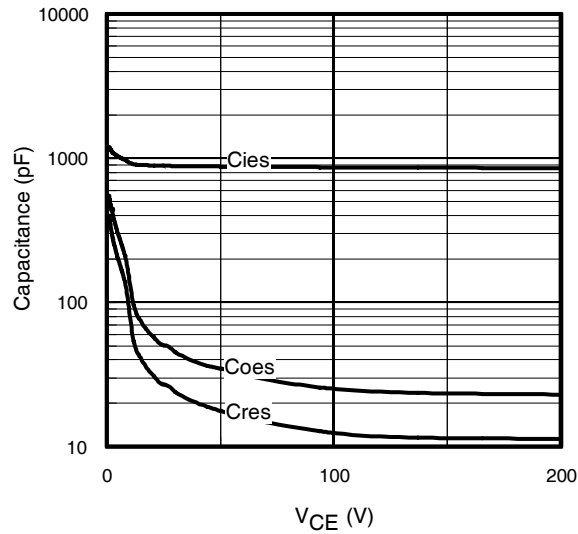


Fig 13. Typical Capacitance vs. Collector-to-Emitter Voltage

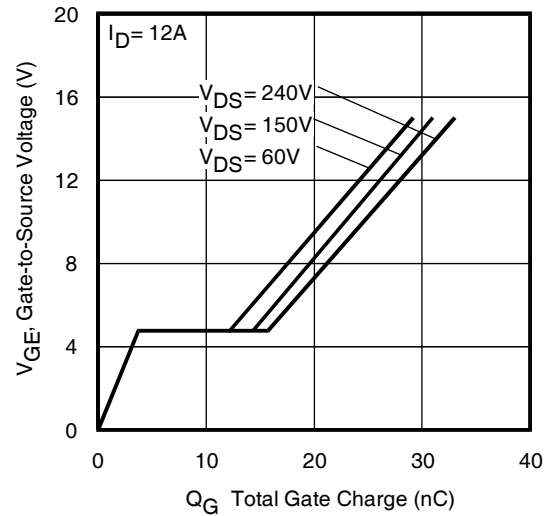


Fig 14. Typical Gate Charge vs. Gate-to-Source Voltage

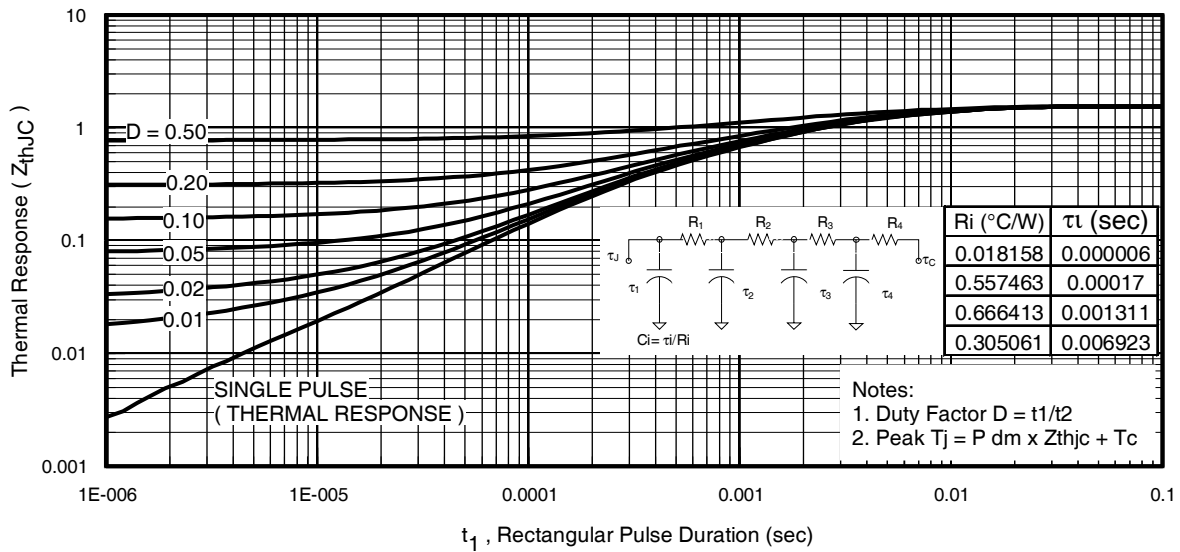


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

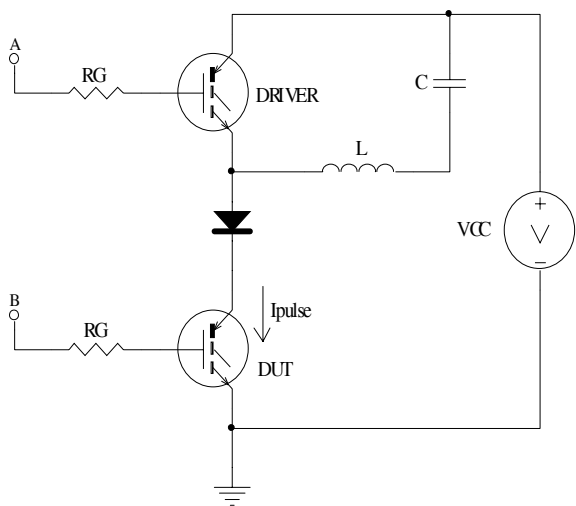


Fig 16a. t_{st} and E_{PULSE} Test Circuit

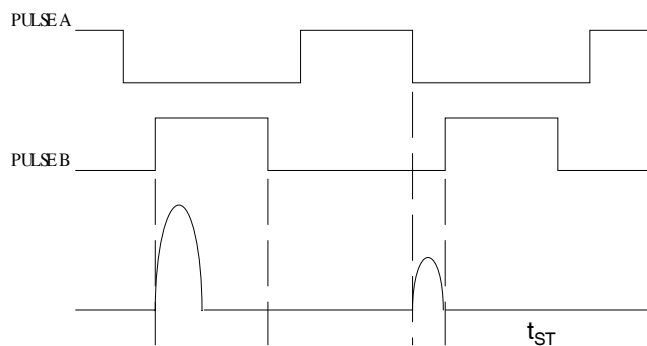


Fig 16b. t_{st} Test Waveforms

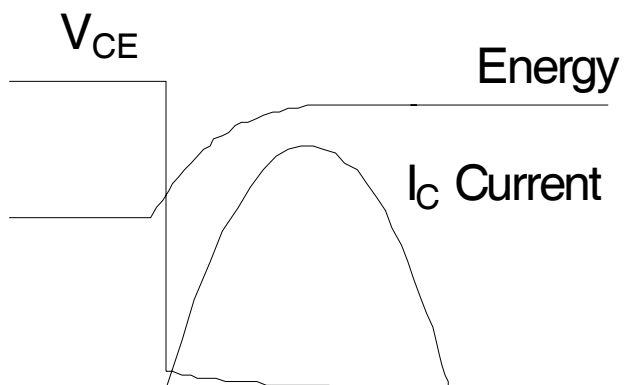


Fig 16c. E_{PULSE} Test Waveforms

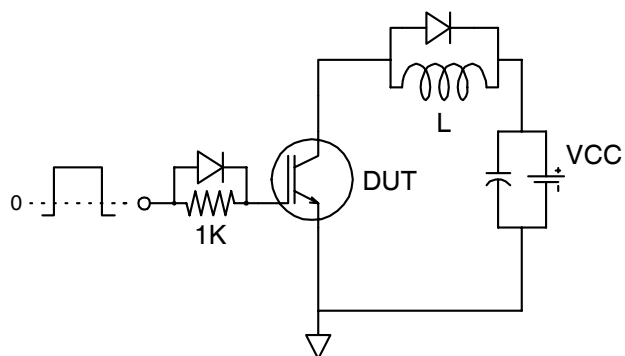
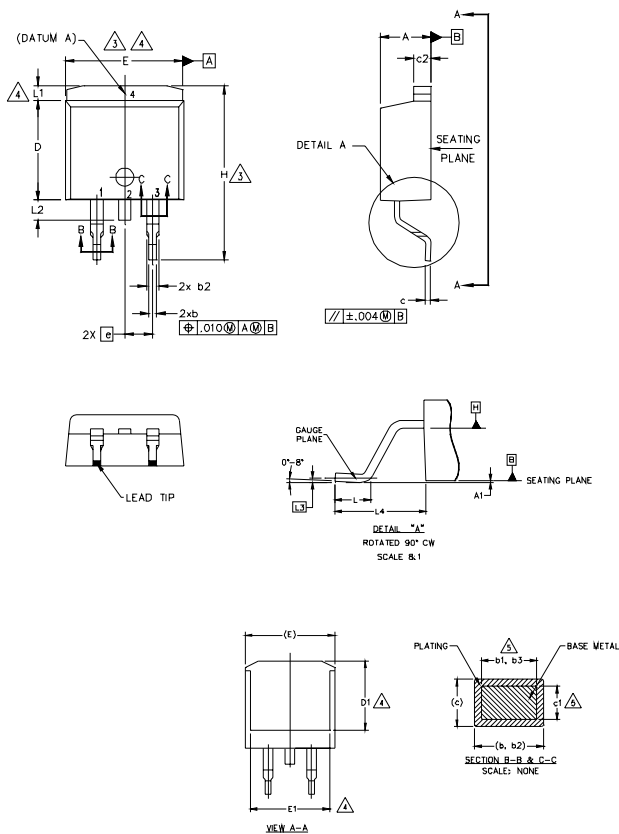


Fig. 17 - Gate Charge Circuit (turn-off)

D²Pak (TO-263AB) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	5
a1	0.00	0.254	.000	.010	
b1	0.51	0.99	.020	.039	
b2	0.51	0.89	.020	.035	5
b3	1.14	1.78	.045	.070	
c	1.14	1.73	.045	.068	
c1	0.38	0.74	.015	.029	5
c2	0.38	0.58	.015	.023	
D	1.14	1.65	.045	.065	
D1	8.38	9.65	.330	.380	3
E	6.86	—	.270	—	4
E1	9.65	10.67	.380	.420	3,4
e	6.22	—	.245	—	4
H	2.54 BSC		.100 BSC		4
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2	—	1.65	—	.066	
L3	1.27	1.78	—	.070	
L4	0.25 BSC		.010 BSC		
	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
2, 4.- DRAIN
3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

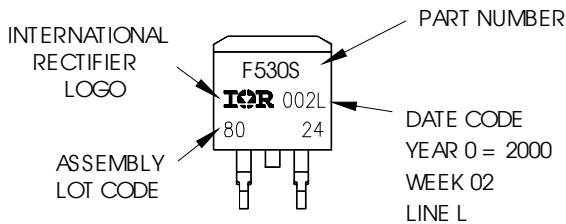
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

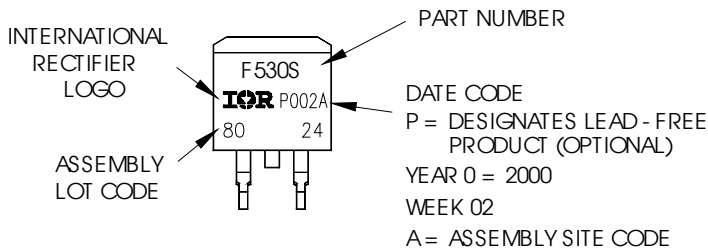
D²Pak (TO-263AB) Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position indicates "Lead - Free"



OR

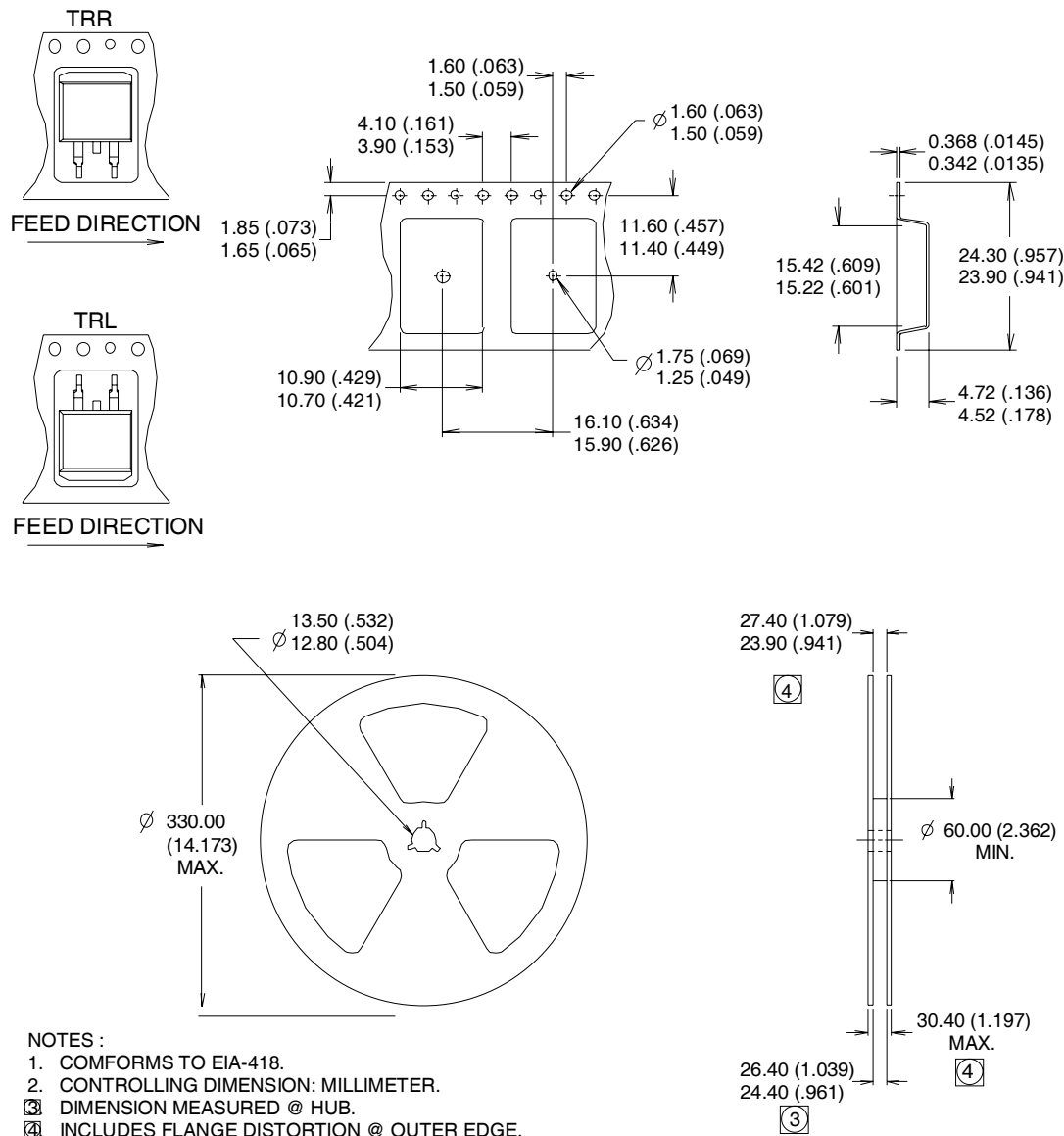


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

www.irf.com

D²Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>